

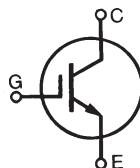
IGBT

Optimized for
switching up to 5KHz

IXGA 12N120A2
IXGP 12N120A2

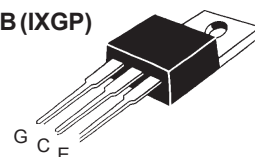
$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 24 \text{ A} \\ V_{CE(sat)} &= 3.0 \text{ V} \end{aligned}$$

Preliminary data sheet

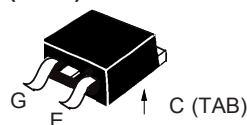


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	24	A
I_{C90}	$T_C = 90^\circ\text{C}$	12	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	48	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 100 \Omega$ Clamped inductive load	$I_{CM} = 24$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	75	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque with screw M3 Mounting torque with screw M3.5	0.45/4 Nm/lb.in. 0.55/5 Nm/lb.in.	
Weight	TO-220	4	g
	TO-263	2	g

TO-220AB (IXGP)



TO-263 AA (IXGA)



Features

- International standard packages
JEDEC TO-220AB and TO-263AA
- Low $V_{CE(sat)}$
- for minimum on-state conduction losses
- MOS Gate turn-on
- drive simplicity

Applications

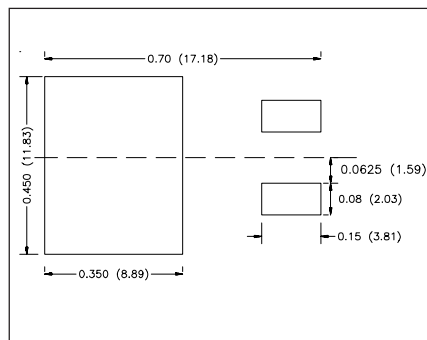
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Capacitor discharge

Advantages

- Easy to mount with one screw
- Reduces assembly time and cost
- High power density

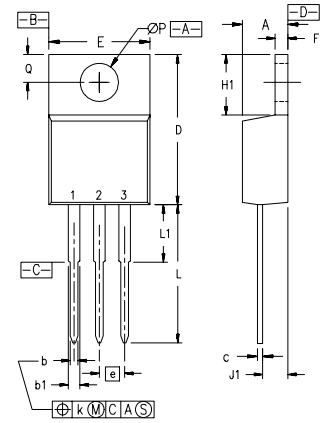
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $T_J = 25^\circ\text{C}$			25 μA
	$V_{GE} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			250 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$		2.4	3.0 V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C90}$, $V_{CE} = 10\text{ V}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	4.0	7.8	S
$I_{C(on)}$	$V_{GE} = 10\text{ V}$, $V_{CE} = 10\text{ V}$		35	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		530	pF
C_{oes}			30	pF
C_{res}			4	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5\text{ V}_{CES}$		24	nC
Q_{ge}			5.5	nC
Q_{gc}			8.8	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 960\text{ V}$, $R_G = R_{off} = 100\ \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8\text{ V}_{CES}$, higher T_J or increased R_G		15	ns
t_{ri}			30	ns
$t_{d(off)}$			680	1000 ns
t_{fi}			650	1000 ns
E_{off}			5.4	9.0 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 960\text{ V}$, $R_G = R_{off} = 100\ \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8\text{ V}_{CES}$, higher T_J or increased R_G		15	ns
t_{ri}			30	ns
E_{on}			0.5	mJ
$t_{d(off)}$			700	ns
t_{fi}			1050	ns
E_{off}			7.7	mJ
R_{thJC}	TO-220			1.66 K/W
R_{thCK}			0.5	K/W



Min. Recommended Footprint
(Dimensions in inches and mm)

TO-220 AB Dimensions

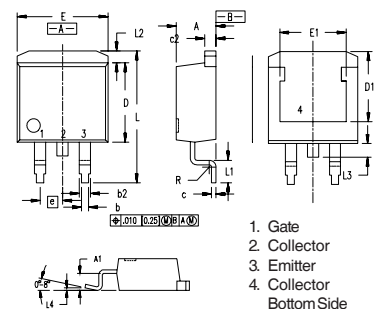


Pins: 1 - Gate
2 - Collector
3 - Emitter
4 - Collector Bottom Side

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

TO-263 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

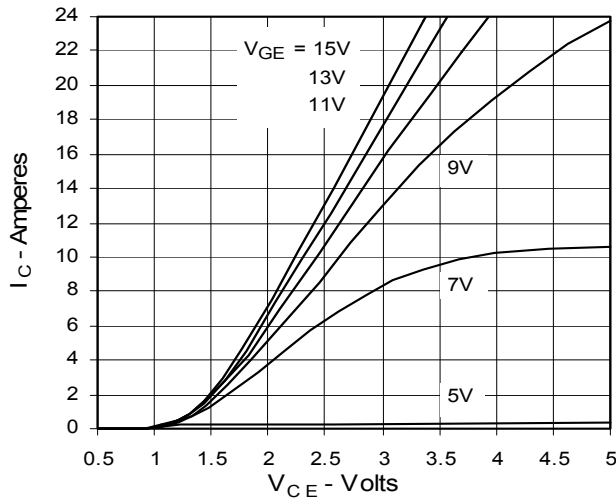
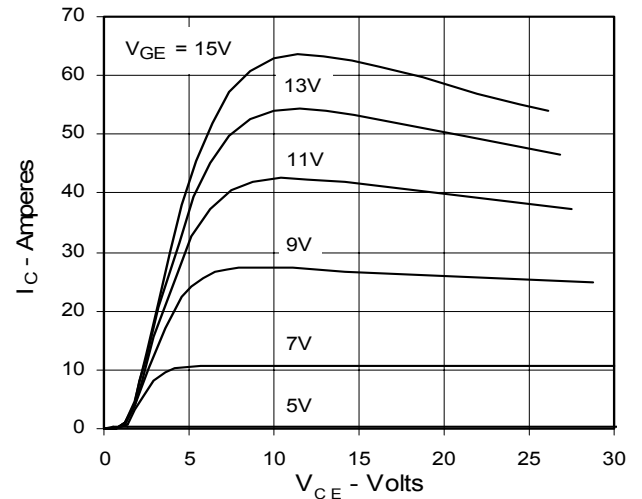
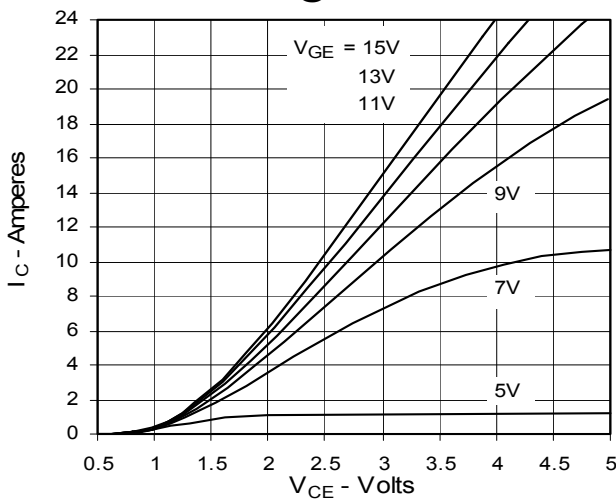
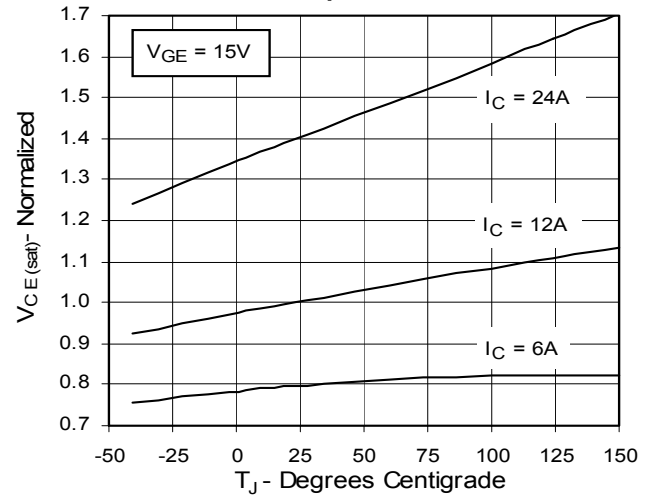
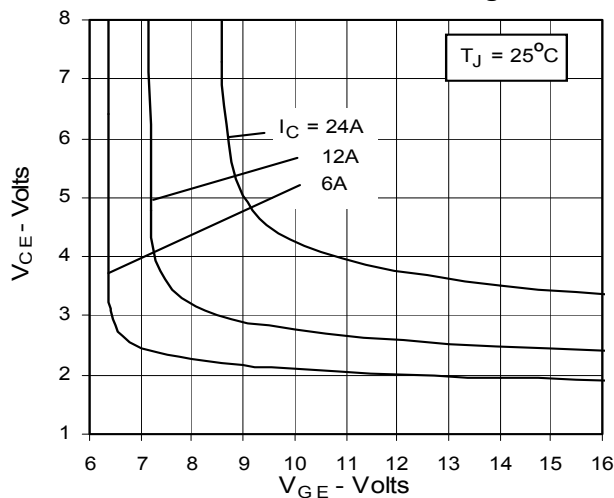
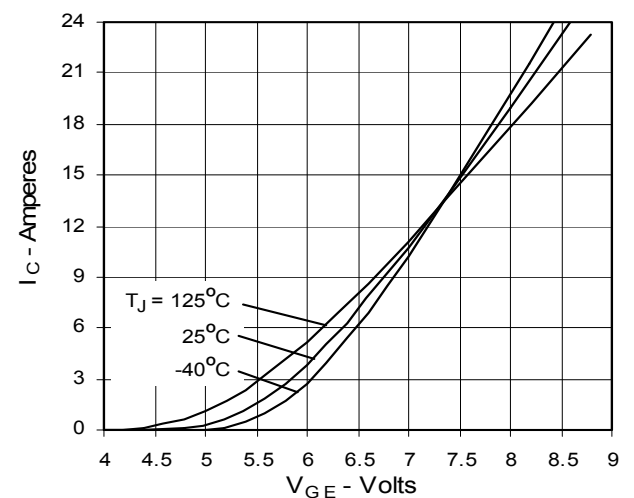
Fig. 1. Output Characteristics
@ 25 °C

Fig. 2. Extended Output Characteristics
@ 25 °C

Fig. 3. Output Characteristics
@ 125 °C

Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

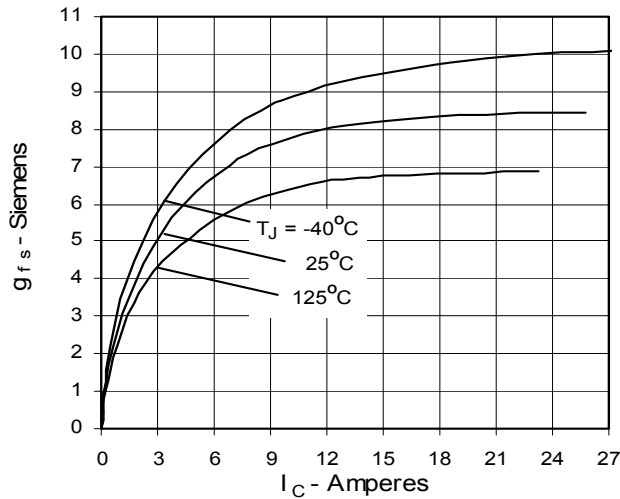


Fig. 8. Dependence of Turn-off Energy Loss on R_G

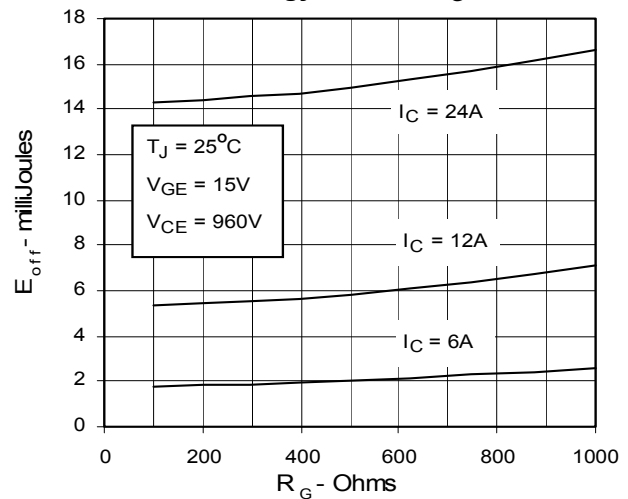


Fig. 9. Dependence of Turn-Off Energy Loss on I_C

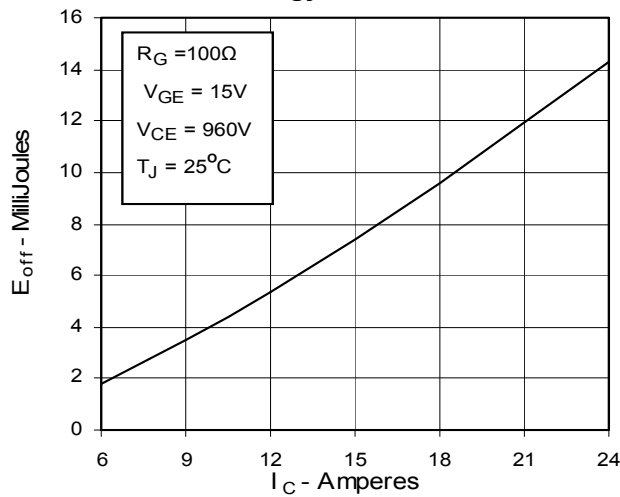


Fig. 10. Dependence of Turn-off Delay Time on R_G

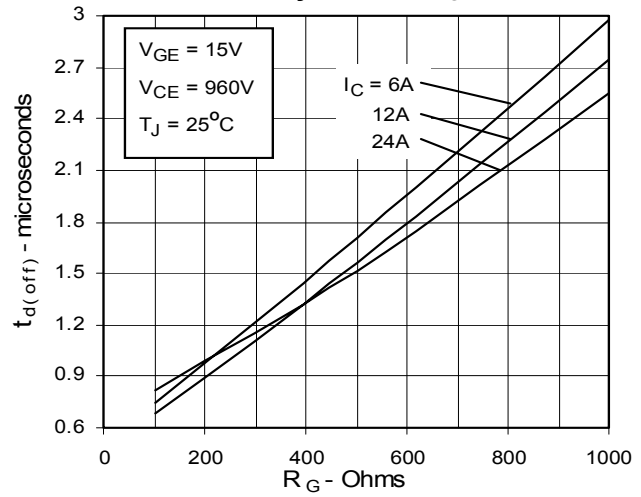


Fig. 11. Dependence of Turn-off Current Fall Time on R_G

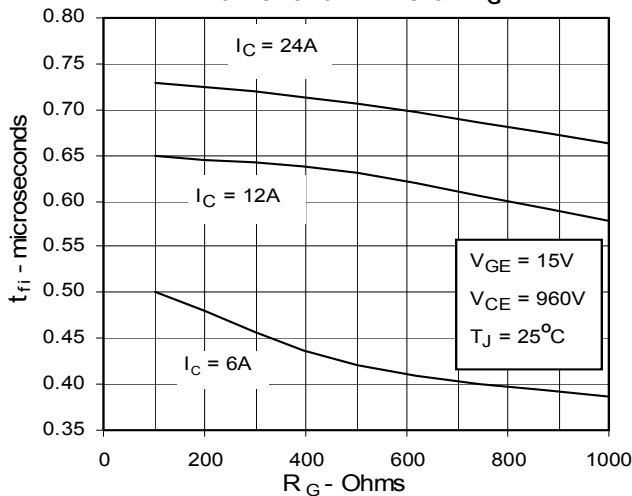


Fig. 12. Dependence of Turn-off Switching Time on I_C

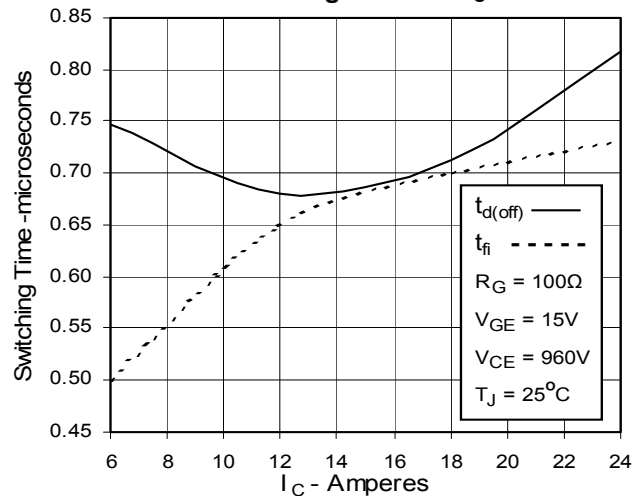


Fig. 13. Gate Charge

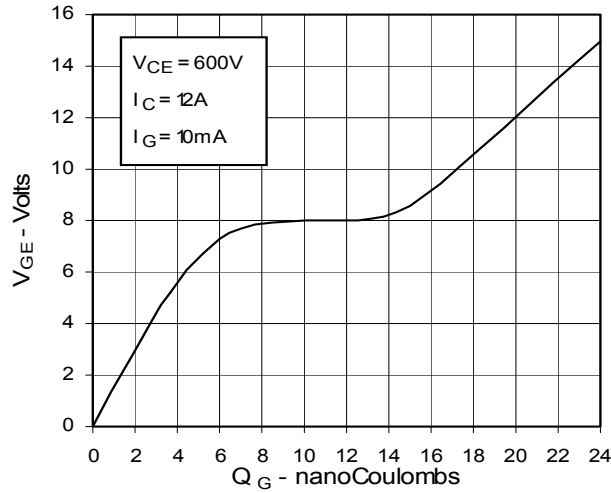


Fig. 14. Reverse-Bias Safe Operating Area

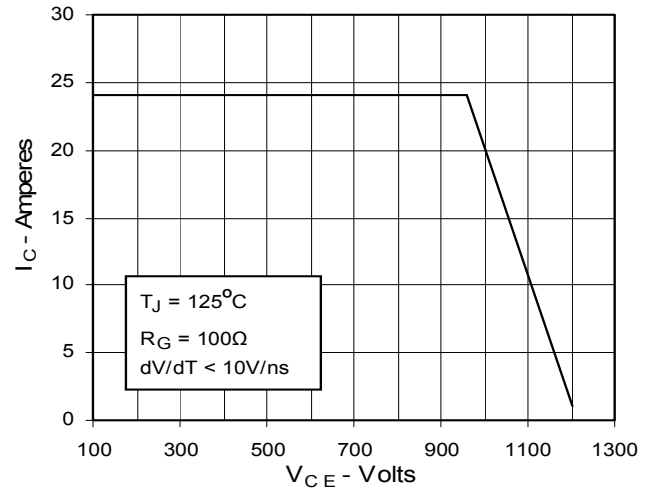


Fig. 15. Capacitance

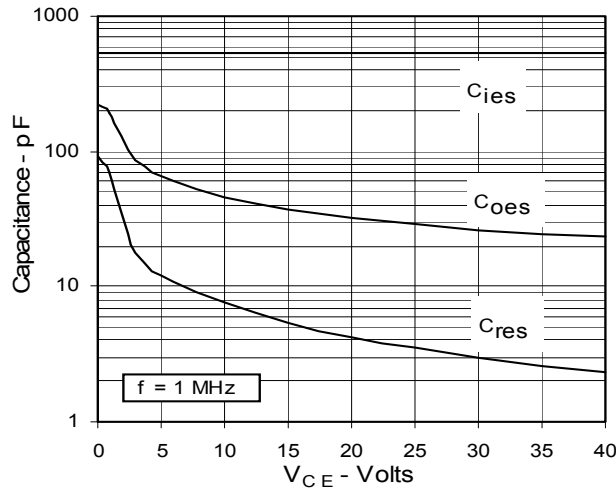


Fig. 17. Maximum Transient Thermal Resistance

